Product data sheet

1. General description

Ultrafast power diode in a 2-lead TO220 plastic package.





2. Features and benefits

- Fast switching
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT
- Package meets UL94V0 which guaranteed by Epoxy Mold Compound

3. Applications

- Active PFC in air conditioner
- · High frequency switched-mode power supplies
- Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes		Values		Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			650		V	
$I_{F(AV)}$	average forward current	$δ = 0.5$; square-wave pulse; $T_{mb} \le 105$ °C; Fig. 1; Fig. 2; Fig. 3		20			А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_{mb} \le$ 105 °C; square-wave pulse		40			Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		180 198		А	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse				Α	
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 20 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.90	2.60	V
		I _F = 20 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.50	2.20	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	26	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		K ——— A
2	Α	anode		K — A 001aaa020
mb	mb	mounting base; connected to cathod		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYV21M-650P	TO220-2L	BYV21M-650PQ	Tube	50	TO220d-2L	13-Oct-2022

7. Marking

Table 4. Marking codes

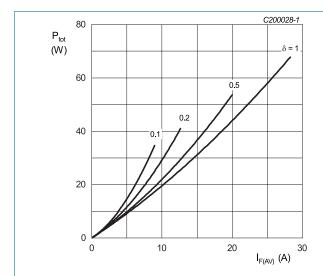
Type number	Marking codes
BYV21M-650P	BYV21M 650P

8. Limiting values

Table 5. Limiting values

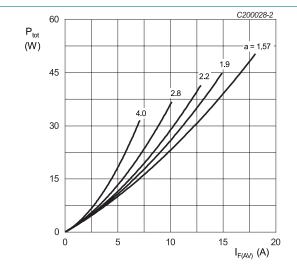
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			650	V
V_{RWM}	crest working reverse voltage			650	V
V_R	reverse voltage	DC		650	V
I _{F(AV)}	average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 105$ °C; Fig. 1; Fig. 2; Fig. 3		20	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 105 °C; square-wave pulse		40	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		180	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		198	Α
T _{stg}	storage temperature			-65 to 175	°C
T _j	junction temperature			-65 to 175	°C



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 1.714 \text{ V; } R_{\text{s}} = 0.0241 \text{ }\Omega \\ \end{split}$$
 Fig. 1. Forward power dissipation as a function of average forward current; square waveform;

maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.714 V; R_s = 0.0241 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

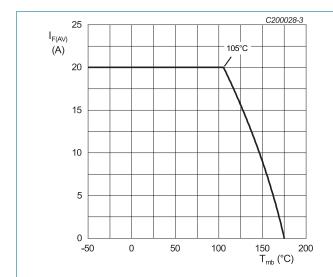


Fig. 3. Forward current as a function of mounting base temperature; maximum values

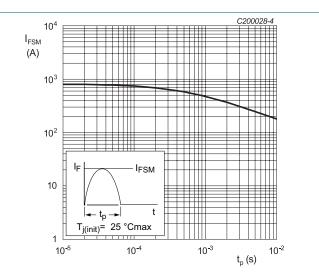


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5		-	-	1.3	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

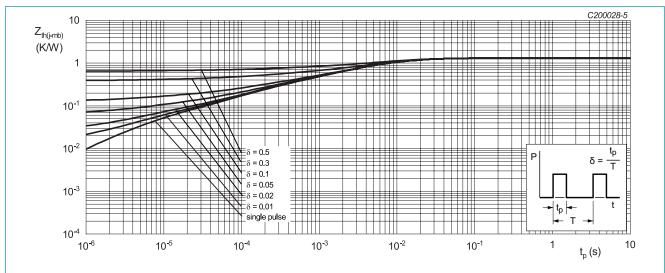
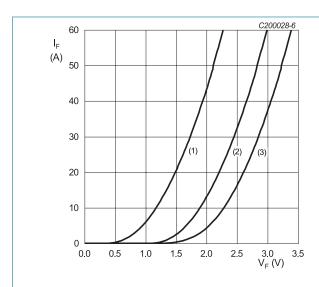


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7 Characteristics

	naracteristics						
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V_{F}	forward voltage	I _F = 20 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.90	2.60	V
		I _F = 20 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.50	2.20	V
I_R	reverse current	V _R = 650 V; T _j = 25 °C		-	0.5	30	μΑ
		V _R = 650 V; T _j = 150 °C		-	-	0.8	mA
Dynamic	characteristics						
Q _r I	reverse charge	$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	85	-	nC
		$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	350	-	nC
t _{rr}	reverse recovery time	$I_F = 0.5 \text{ A}; I_{rr} = 0.25 \text{ A}; I_R = 1 \text{ A}; T_j = 25 \text{ °C}$		-	28	-	ns
		$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	26	-	ns
		$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	50	-	ns
		$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 ^{\circ}\text{C}; Fig. 7$		-	90	-	ns
I _{RM}	peak reverse recovery current	$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	3.6	-	А
		$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 ^{\circ}\text{C}; Fig. 7$		-	7.5	-	А
E _{as}	non-repetitive analanche energy	T _j = 25 °C		16.8	-	-	mJ



 V_o = 1.714 V; R_s = 0.0241 Ω

(1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig. 6. Forward current as a function of forward voltage

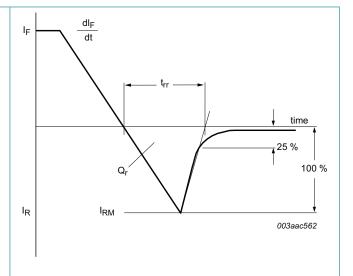
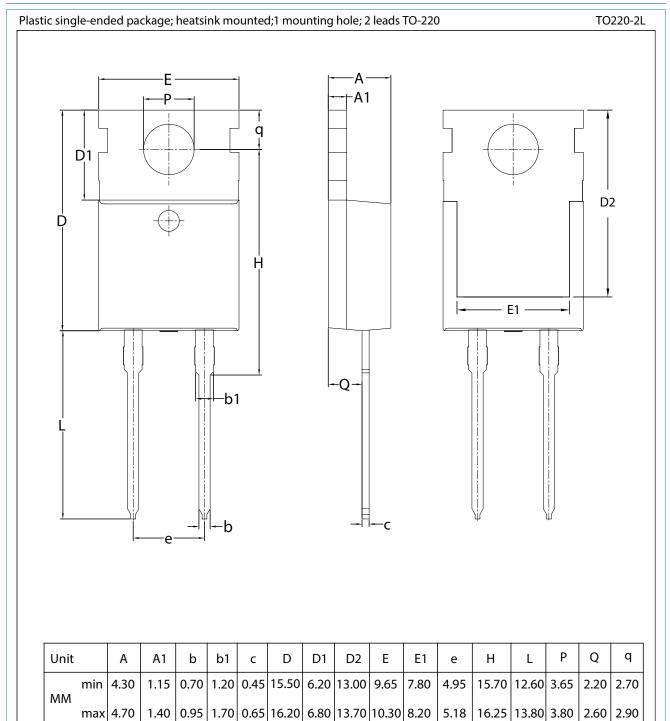


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



Note:

1. All dimensions don't include mold flash and metal protrusion.

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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BYV21M-650P

Ultrafast power diode

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